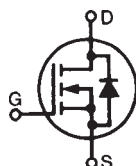


PolarHV™ Power MOSFET

IXTA 5N60P
IXTP 5N60P

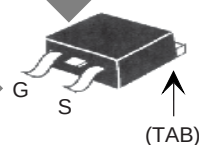
$$\begin{aligned} V_{DSS} &= 600 \text{ V} \\ I_{D25} &= 5 \text{ A} \\ R_{DS(on)} &\leq 1.7 \text{ } \Omega \end{aligned}$$

N-Channel Enhancement Mode
Avalanche Rated

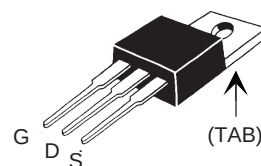


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 175^\circ\text{C}$	600	V
V_{DGR}	$T_J = 25^\circ\text{C to } 175^\circ\text{C}; R_{GS} = 1 \text{ M}\Omega$	600	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	5	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	10	A
I_{AR}	$T_C = 25^\circ\text{C}$	5	A
E_{AR}	$T_C = 25^\circ\text{C}$	20	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	360	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 18 \text{ } \Omega$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	100	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10 s	260	$^\circ\text{C}$
M_d	Mounting torque (TO-220)	1.13/10	Nm/lb.in.
Weight	TO-220	4	g
	TO-263	3	g

TO-263 (IXTA)



TO-220 (IXTP)



G = Gate
S = Source

D = Drain
TAB = Drain

Features

- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

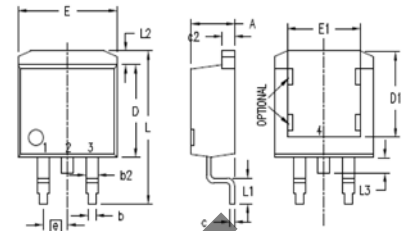
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \text{ } \mu\text{A}$	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 50 \text{ } \mu\text{A}$	3.0		5.5 V
I_{GSS}	$V_{GS} = \pm 30 \text{ V}$, $V_{DS} = 0 \text{ V}$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$			5 μA
	$V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			50 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \text{ } \mu\text{s}$, duty cycle $d \leq 2 \%$			1.7 Ω

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{ V}$; $I_D = 0.5 I_{D25}$, pulse test	3.0	5.0	S
C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$		750	pF
C_{oss}			78	pF
C_{rss}			6.3	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 V_{DSS}$, $I_D = 0.5 I_{D25}$ $R_G = 18\ \Omega$ (External)		22	ns
t_r			24	ns
$t_{d(off)}$			55	ns
t_f			17	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 V_{DSS}$, $I_D = 0.5 I_{D25}$		14.2	nC
Q_{gs}			4.8	nC
Q_{gd}			4.8	nC
R_{thJC}	(TO-220)			1.25 $^\circ\text{C/W}$
R_{thCS}			0.25	$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{ V}$			5 A
I_{SM}	Repetitive			15 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{ V}$, $I_F = 5\text{ A}$, $-di/dt = 100\text{ A}/\mu\text{s}$			1.5 V
t_{rr}	Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$		500	ns

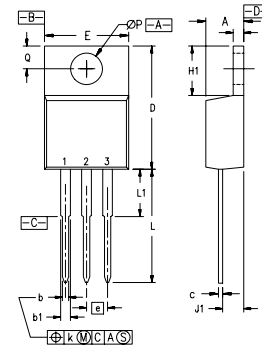
TO-263 (IXTA) Outline



1. GATE
2. DRAIN (COLLECTOR)
3. SOURCE (EMITTER)
4. DRAIN (COLLECTOR)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

TO-220 (IXTP) Outline



- Pins: 1 - Gate 2 - Drain
3 - Source 4 - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585
one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2

Fig. 1. Output Characteristics
@ 25°C

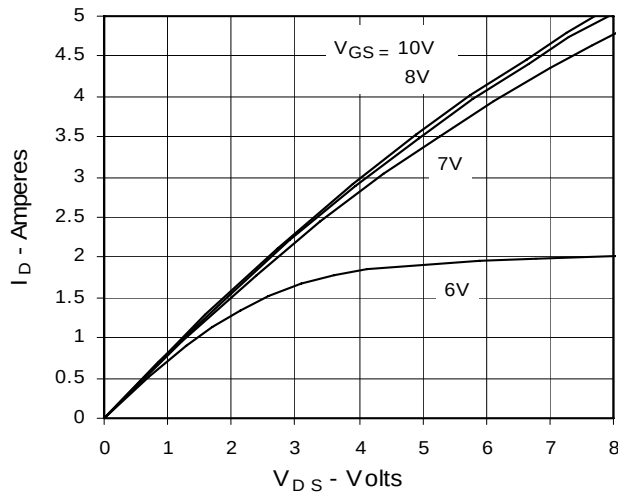


Fig. 2. Extended Output Characteristics
@ 25°C

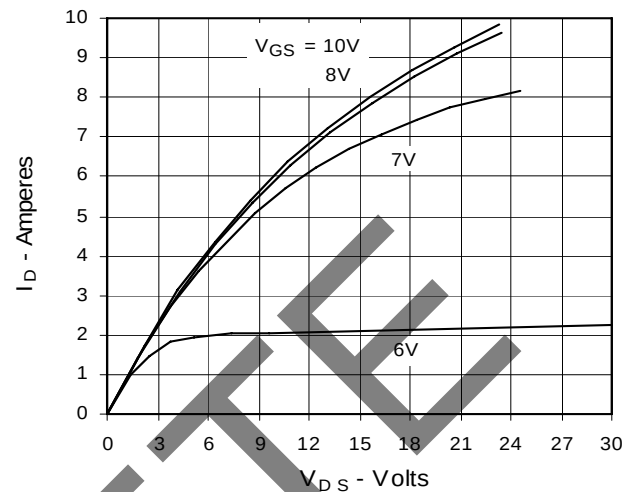


Fig. 3. Output Characteristics
@ 125°C

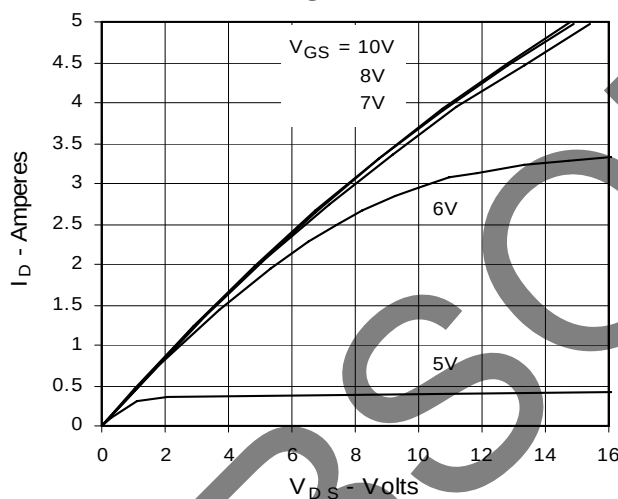


Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Junction Temperature

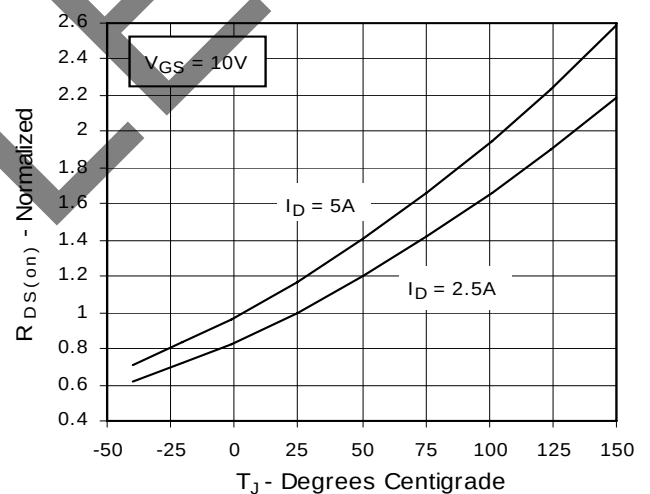


Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. I_D

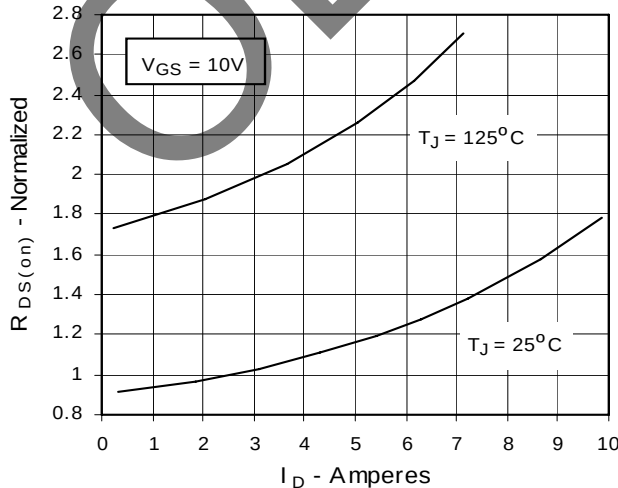


Fig. 6. Drain Current vs. Case Temperature

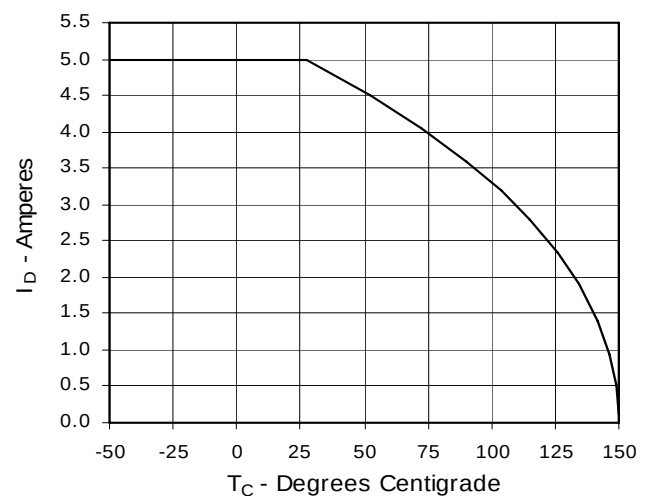


Fig. 7. Input Admittance

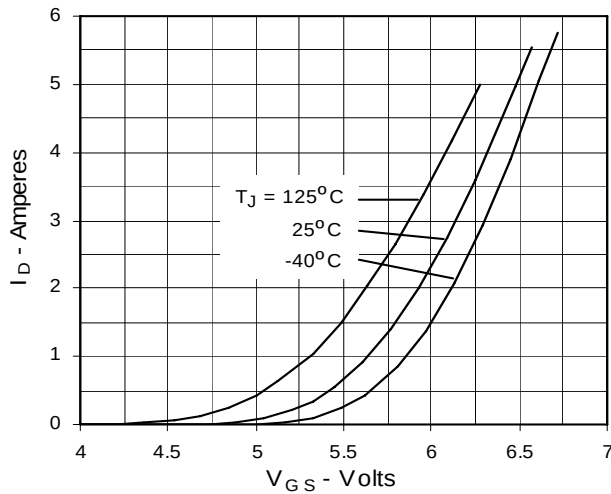


Fig. 8. Transconductance

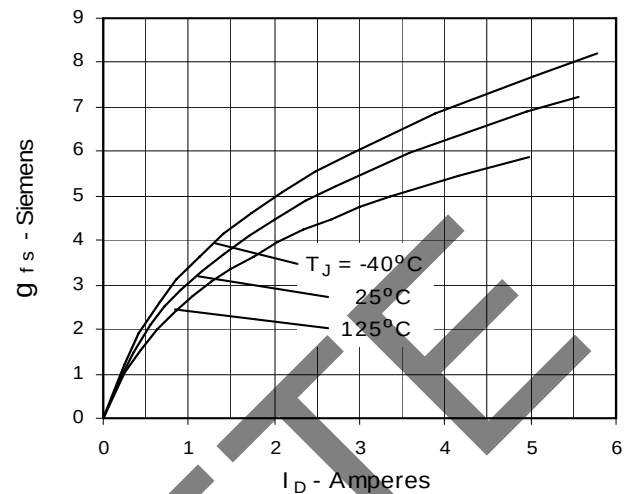


Fig. 9. Source Current vs. Source-To-Drain Voltage

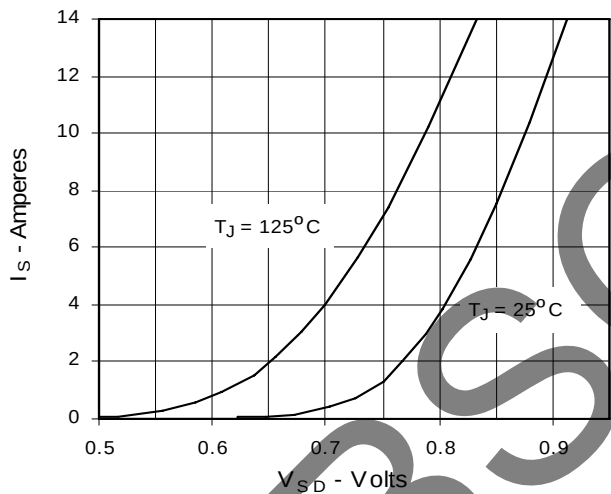


Fig. 10. Gate Charge

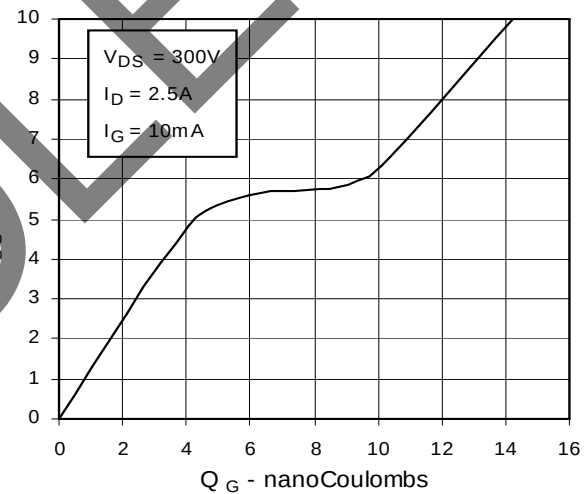


Fig. 11. Capacitance

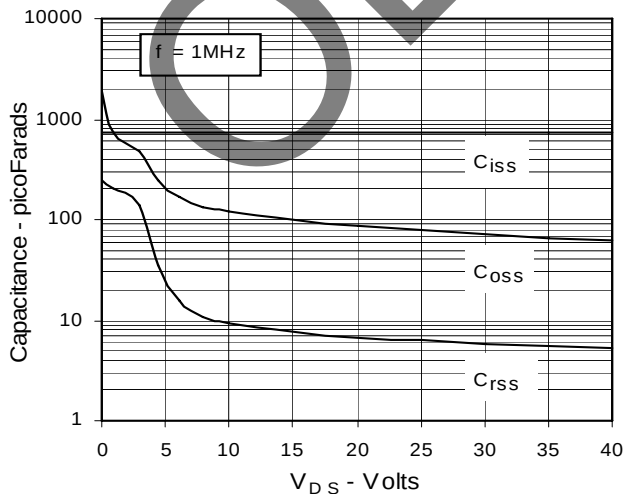
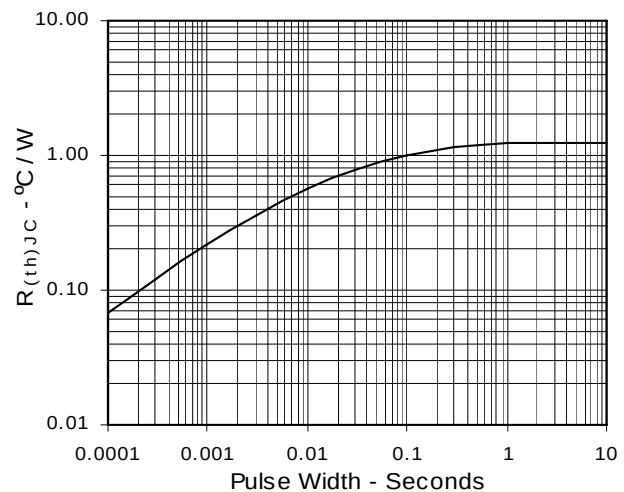


Fig. 12. Maximum Transient Thermal Resistance





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